

INFLUENCE OF DEFORMATION EFFECTS
ON ELECTRICAL PROPERTIES OF STRUCTURE
METAL-SEMICONDUCTOR-DOPED
SEMICONDUCTOR

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S u m m a r y

The influence of elastic deformations that arise owing to a mismatch between the lattice parameters of contacting semiconductor materials and in a vicinity of the defect cluster induced by interstitial cadmium in a doped semiconductor CdTe substrate on the electron injection into the insulating layer of the metal-undoped $Zn_xCd_{1-x}Te$ semiconductor- n -CdTe semiconductor substrate structure has been studied.